

Theoretical Study on New Types of Noble-Gas Containing Anions and ClLiClNgO⁻ (Ng = Ar, Kr and Xe) Yu-Ting Lin, Chin-Mei Liao and Wei-Ping Hu *

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Abstract

We study a new type of noble-gas containing anions ClLiClNgO⁻ (Ng = Ar, Kr, Xe), which are complexes between the superhalogen ClLiCl⁻ and NgO. We expect that ClLiClNgO⁻ to be ion-dipole complexes (ClLiCl⁻...NgO) and discussing the impact of superhalogen ClLiCl⁻ on NgO. The structures, energies, and electron density are calculated by a high-level theoretical method.

The results show that the stability of ClLiClNgO⁻ are determined by two decomposition pathways: the (P1) pathway is endoergic by 11.9 kcal/mol for Ng = Ar. The barrier of the (P4) pathway is 7.9 kcal/mol for Ng = Ar.

Moreover, for (P3) pathway, the rates of intersystem crossing would be limited by the thermal activation to the crossing points. The triplet state now crosses at much larger Ar–O distance (0.150 Å longer than equilibrium bond distance) where the energy is ~3 kcal/mol higher.

51.7 (67.2) [88.6]

Introduction

In recent studies, superhalogen-stabilized noble gas compounds predicted¹ and the noble-gas prefer to form anions $FNgO^{-2}$, $F^{-}(NgO)_n^{-3}$, the result shows fluoride ion can induce Ng–O bonds. Thus, we design a new type of noble-gas containing anions and including superhalogen ClLiCl⁻, which haven't been studied. The structures, stability, electron density distribution of the noble-gas containing anions ClLiClNgO⁻ will be investigated.

Methods

MP2 and CCSD(T) electronic structure theory are used, and the basis sets are used Dunning-type aug-cc-pVnZ (abbreviated as apnz)⁴. The electronic structure calculations were performed using the Gaussian 16 program, revision C01 and electron density profiles using Multiwfn.⁵

Results and Discussion



Electron density distribution

From electron density profile (figure 3) and NBO charge distribution (Figure 1), ClLiCl⁻ can

Structures

In figure 1, the structures of ClLiClNgO⁻ (Ng = Ar, Kr, Xe) are linear and nonlinear, depending on the different theoretical methods we use. The bond length of Cl–Ng are 2.994~3.077 Å, Ng–O are 1.719~1.929 Å. We know that the Cl–Ng and Ng–O bond length of ClLiClNgO⁻ increases with the increase of noble gas atomic number. For XNgO⁻ (X =ClLiCl, F and Cl, Ng = Ar, Kr, Xe) when increasing of noble gas atomic number, if we compare ClLiClNgO⁻ with FNgO⁻: (a) X–NgO⁻ increase 0.753, 0.754 and 0.784 Å, respectively; compare ClLiClNgO⁻ with ClNgO⁻ (a) X–NgO⁻ slightly increase 0.158, 0.165 and 0.172 Å. (b) XNg–O⁻ increase 0.009 Å, decrease 0.013 and 0.029 Å when compare with FNgO⁻ and compare with ClNgO⁻ (b) XNg–O⁻ increase 0.003 Å, decrease 0.008 and 0.017 Å. They have not changed significantly.



induce Ng–O bonds: ClLiCl⁻...Ng=O, like FNgO⁻ are ion-dipole interaction: F⁻...Ng=O.



Figure 3. Contour plots of the calculated electron density of ClLiClNgO⁻.

Figure 1. The structures of ClLiClNgO⁻, unit: Å and °. NBO charge (in red).

Stability

In Figure 2, we consider all the most plausible dissociation pathways. (P1) ClLiClNgO⁻ \rightarrow ClLiCl⁻ + NgO (P1-1) ClLiClNgO⁻ \rightarrow ClLiCl⁻ + Ng + O(S) (P2) ClLiClNgO⁻ \rightarrow ClLiCl⁻ + Ng + O⁻(D) (P3) ClLiClNgO⁻ \rightarrow ClLiCl⁻ + Ng + O(T) (P4) ClLiClNgO⁻ \rightarrow ClLiOCl⁻ + Ng For ClLiClNgO⁻, the Ng–O bond energies (P1-1) is nearly equal to Ng–O of ONg (P0: ONg \rightarrow O + Ng). This implies that ClLiClNgO⁻ does not affect bond energies of Ng–O. This study investigated the structures and stability of ClLiClNgO⁻. When noble gas atoms are Ar, Kr and Xe, the anion molecules are found to be stable at low temperature.

Importantly, a new type of noble-gas containing anions and including superhalogen ClLiCl⁻. ClLiClNgO⁻ were stable by ion-dipole interaction (ClLiCl⁻...Ng=O). In the future, it will be possible to design types of noble-gas containing anions on different types of superhalogen molecules.

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